**Product data sheet** 

## 1. General description

Silicon Carbide Schottky diode in a DFN 8\*8 plastic package, designed for high frequency switched-mode power supplies.



#### 2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I<sub>FSM</sub>
- Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

### 3. Applications

- · Power factor correction
- · Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			650		V	
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>c</sub> ≤ 157 °C; Fig. 1; Fig. 2; Fig. 3		6		А	
$T_j$	junction temperature			-55 to 175		°C	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.26	1.40	V
		I <sub>F</sub> = 6 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.35	1.55	V
Dynamic	Dynamic characteristics						
Q <sub>r</sub>	recovered charge	$I_F = 6 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 7$		-	13.5	-	nC

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[	κ_I/I_Δ
2	n.c.	not connected	5	K — A 001aaa020
3	А	anode		
4	А	anode	<u>8</u>	
5	К	mounting base; connected to cathode	1 2 3 4	

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC6D06650T	DFN8*8	WNSC6D06650T6J	Таре	3000	DFN8X8N	25-Dec-2019

## 7. Marking

#### **Table 4. Marking codes**

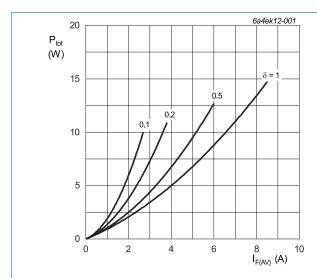
Type number	Marking codes
WNSC6D06650T	WNSC6D 06650T

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Notes	Values	Unit
repetitive peak reverse voltage			650	V
crest working reverse voltage			650	V
reverse voltage	DC		650	V
average forward current	$\delta$ = 0.5; square-wave pulse; T <sub>c</sub> ≤ 157 °C; Fig. 1; Fig. 2; Fig. 3		6	Α
repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>c</sub> ≤ 157 °C; square-wave pulse		12	А
non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		45	Α
forward current	$t_p$ = 10 $\mu$ s; $T_{j(init)}$ = 25 °C; square-wave pulse		510	Α
I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 10  \text{ms}$		10.125	A <sup>2</sup> s
storage temperature			-55 to 175	°C
junction temperature			-55 to 175	°C
	repetitive peak reverse voltage crest working reverse voltage reverse voltage average forward current repetitive peak forward current non-repetitive peak forward current l²t for fusing storage temperature	repetitive peak reverse voltage crest working reverse voltage peak reverse voltage crest working reverse voltage peak reverse voltage peak forward current $\delta = 0.5$ ; square-wave pulse; $T_c \le 157$ °C; Fig. 1; Fig. 2; Fig. 3 $\delta = 0.5$ ; $t_p = 25 \mu s$ ; $t_p = 157 \nu c$ ; square-wave pulse peak forward current peak forward current $t_p = 10 \mu s$ ; $t_{j(init)} = 25 \nu c$ ; sine-wave pulse $t_p = 10 \mu s$ ; $t_{j(init)} = 25 \nu c$ ; square-wave pulse $t_p = 10 \mu s$ ; $t_{j(init)} = 25 \nu c$ ; square-wave pulse storage temperature	repetitive peak reverse voltage crest working reverse voltage per per per per per per per per per pe	repetitive peak reverse voltage



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 0.817 \text{ V; } R_{\text{s}} = 0.1079 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

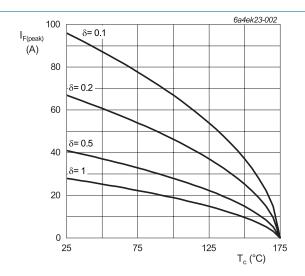
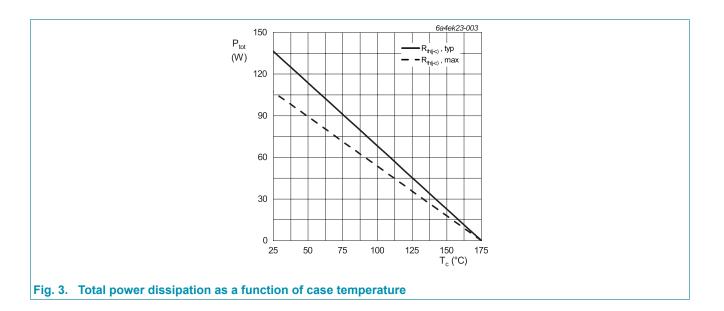


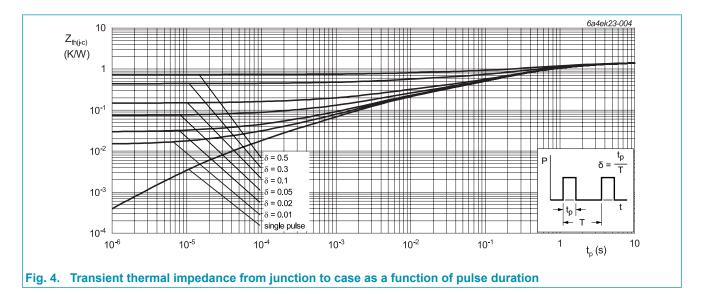
Fig. 2. Current derating as a function of case temperature



#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

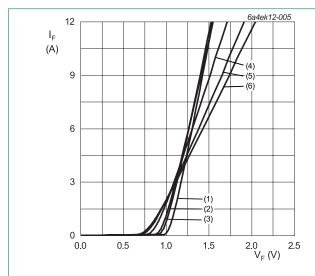
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	Fig. 4		-	1.1	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						'
$V_{F}$	forward current	I <sub>F</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.26	1.40	V
		I <sub>F</sub> = 6 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.35	1.55	V
		I <sub>F</sub> = 6 A; T <sub>j</sub> = 175 °C; <u>Fig. 5</u>		-	1.40	1.60	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	0.6	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; <u>Fig. 6</u>		-	9	120	μA
Dynamic	characteristics			,			1
Q <sub>r</sub>	recovered charge	$I_F = 6 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	13.5	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C		-	325	-	pF
		f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C		-	35	-	pF
		f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C		-	32	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	I <sub>R</sub> = 4 A; L = 5 mH; T <sub>j(init)</sub> = 25 °C		40	-	-	mJ



 $V_o$  = 0.817 V;  $R_s$  = 0.1079  $\Omega$ 

(1)  $T_j$  = -55 °C; typical values

(2)  $T_j = 0$  °C; typical values

(3) T<sub>i</sub> = 25 °C; typical values

(4)  $T_i = 100 \,^{\circ}\text{C}$ ; typical values

(5) T<sub>j</sub> = 150 °C; typical values (6) T<sub>j</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

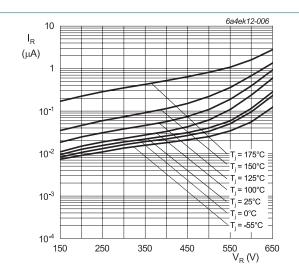
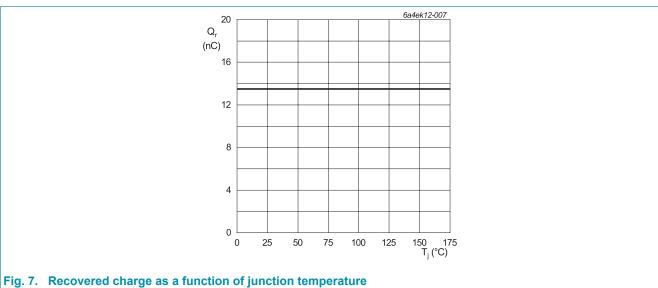
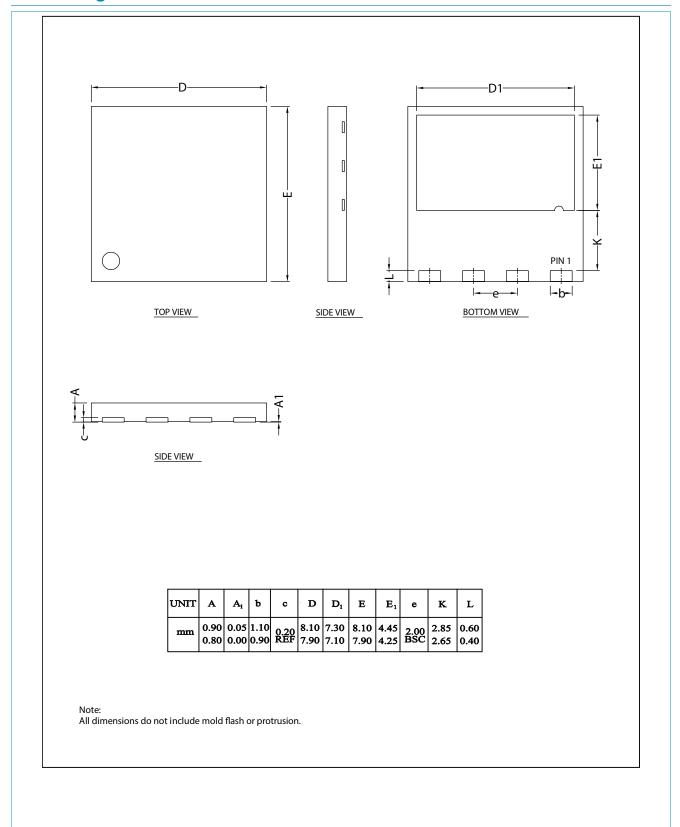


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



## 11. Package outline



### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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